ALPHA & OMEGA
SEMICONDUCTOR

AON3419

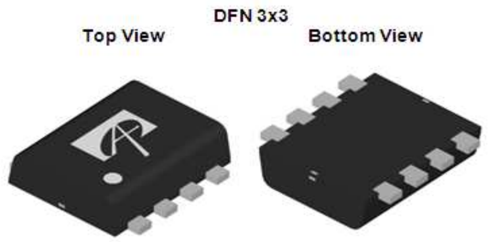
30V P-Channel MOSFET

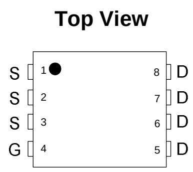
General Description

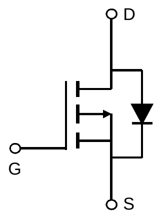
The AON3419 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

Product Summary

V_{DS}	-30V
I_D (at V_{GS}=-10V)	-10A
$R_{DS(ON)}$ (at V_{GS}=-10V)	< 19mΩ
$R_{DS(ON)}$ (at V_{GS} =-4.5V)	< 32mΩ







Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25℃	I_D	-10	A
	T_C=70℃		-7.8	
Pulsed Drain Current [C]		I_{DM}	-45	
Power Dissipation [B]	T_C=25℃	P_D	3.1	W
	T_C=70℃		2	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	℃

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	30	40	℃/W
Maximum Junction-to-Ambient [A D]	Steady-State		65	80	℃/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	30	40	℃/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V		-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0V				-1	µA
			T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V				±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250µA		-1.5	-2.0	-2.5	V
$I_{D(ON)}$	On state drain current	V_{GS}=-10V, V_{DS}=-5V		-45			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V, I_D=-10A			15.5	19	mΩ
			T_J=125°C		22.5	27	
		V_{GS}=-4.5V, I_D=-7A			25	32	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-10A			27		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V			-0.75	-1	V
I_S	Maximum Body-Diode Continuous Current					-4	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-15V, f=1MHz			1040		pF
C_{oss}	Output Capacitance				180		pF
C_{rss}	Reverse Transfer Capacitance				125		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz			4	8	Ω
SWITCHING PARAMETERS							
Q_g(10V)	Total Gate Charge	V_{GS}=-10V, V_{DS}=-15V, I_D=-10A			19	30	nC
Q_g(4.5V)	Total Gate Charge				9.6	20	nC
Q_{gs}	Gate Source Charge				3.5		nC
Q_{gd}	Gate Drain Charge				4.5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-10V, V_{DS}=-15V, R_L=1.5Ω, R_{GEN}=3Ω			10		ns
t_r	Turn-On Rise Time				5.5		ns
$t_{D(off)}$	Turn-Off DelayTime				26		ns
t_f	Turn-Off Fall Time				9		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-10A, dI/dt=500A/µs			11.5		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-10A, dI/dt=500A/µs			25		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t ≤ 10s value and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J =25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. The maximum current rating is package limited.
H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

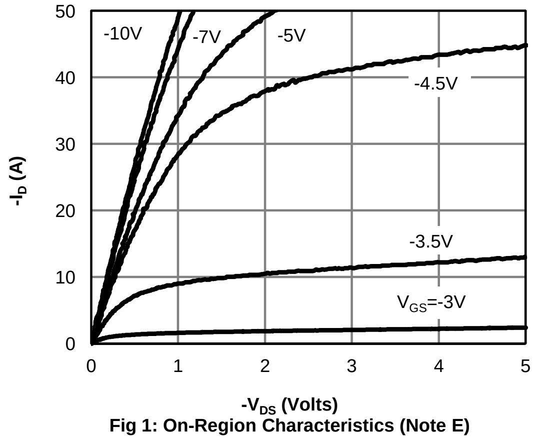


Fig 1: On-Region Characteristics (Note E)

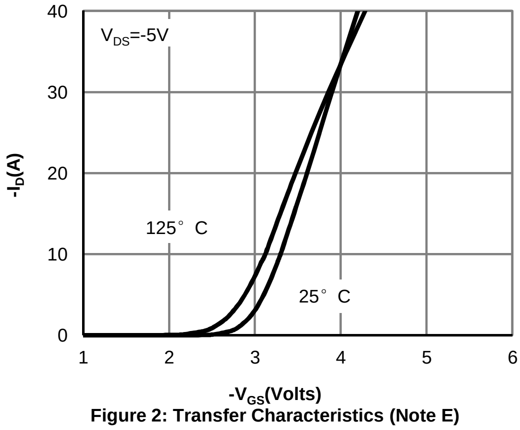


Figure 2: Transfer Characteristics (Note E)

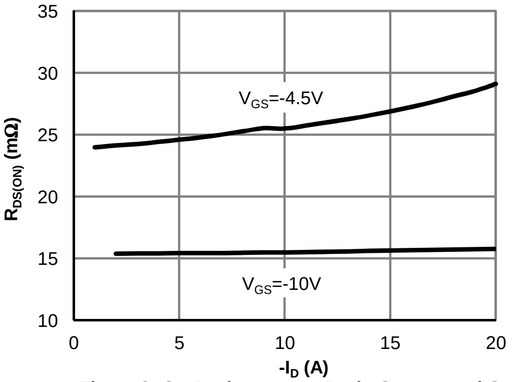


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

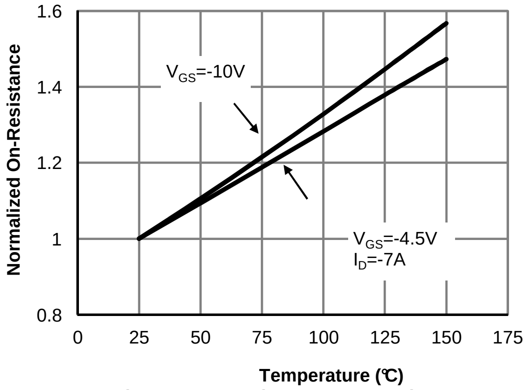


Figure 4: On-Resistance vs. Junction Temperature (Note E)

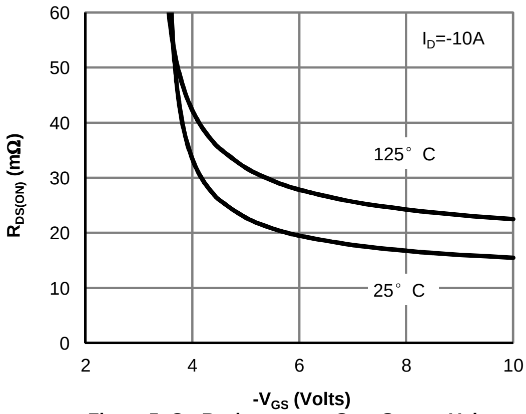


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

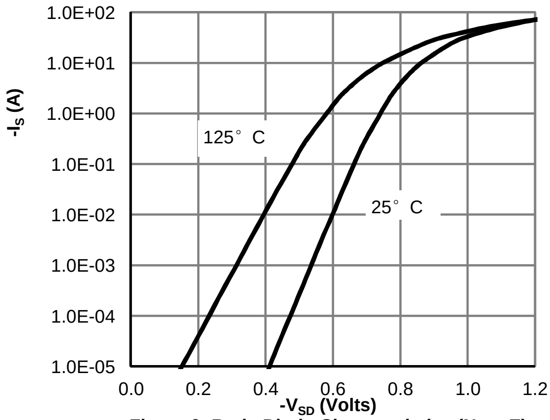


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

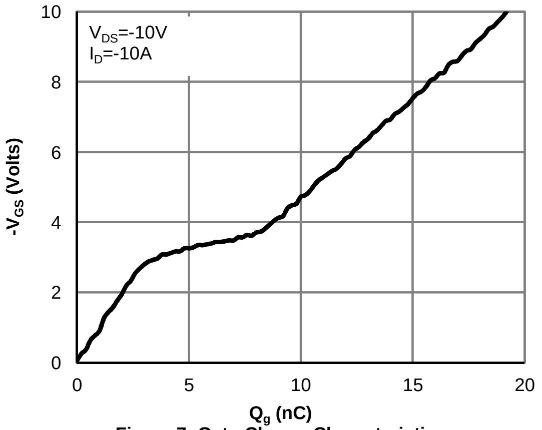


Figure 7: Gate-Charge Characteristics

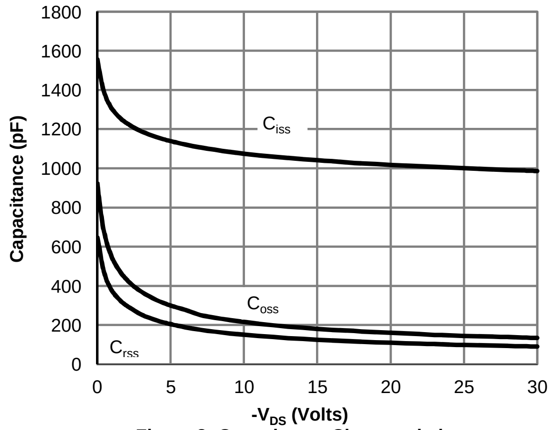
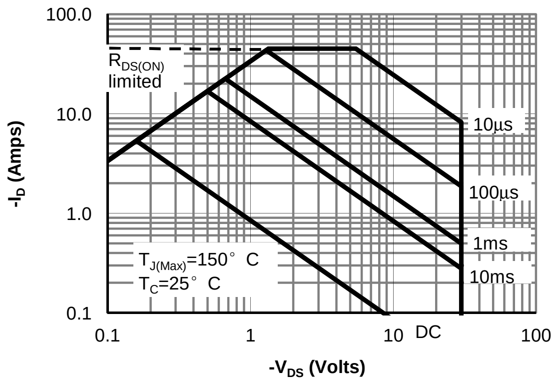
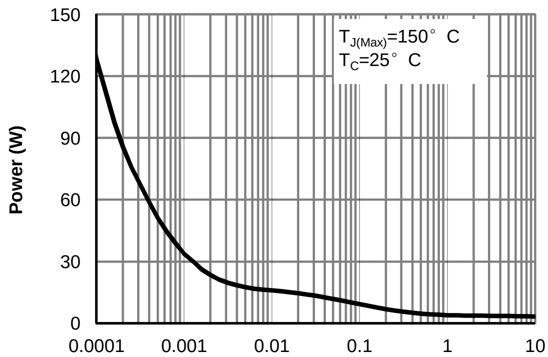


Figure 8: Capacitance Characteristics



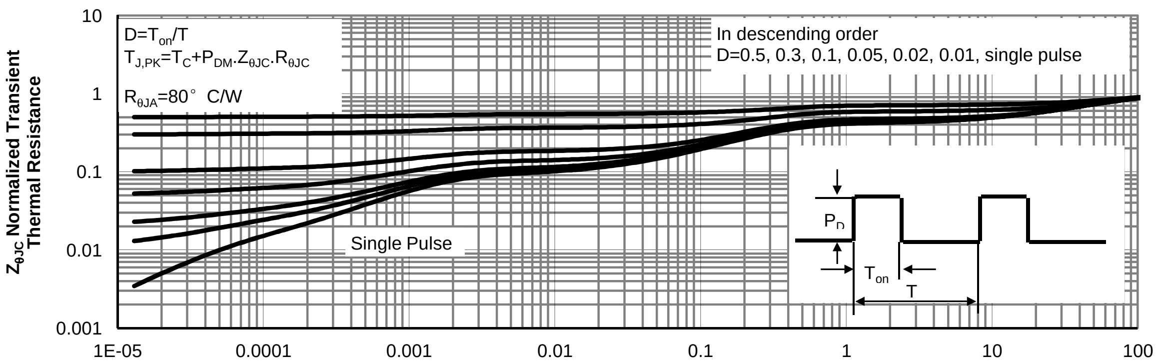
V_{GS}> or equal to 4.5V

Figure 9: Maximum Forward Biased Safe Operating Area (Note F)



Pulse Width (s)

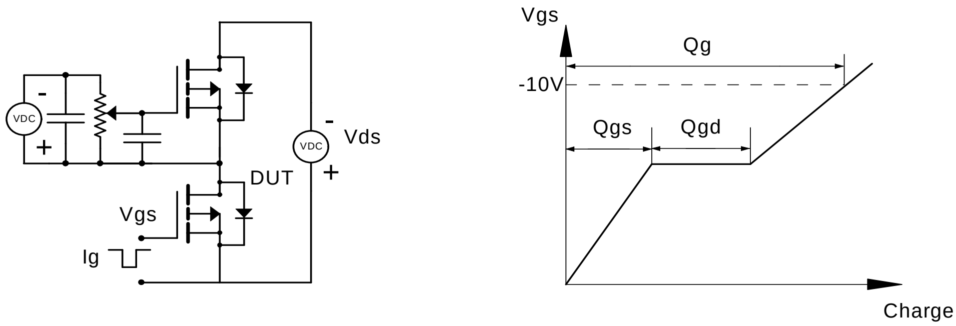
Figure 10: Single Pulse Power Rating Junction-to-Ca (Note F)



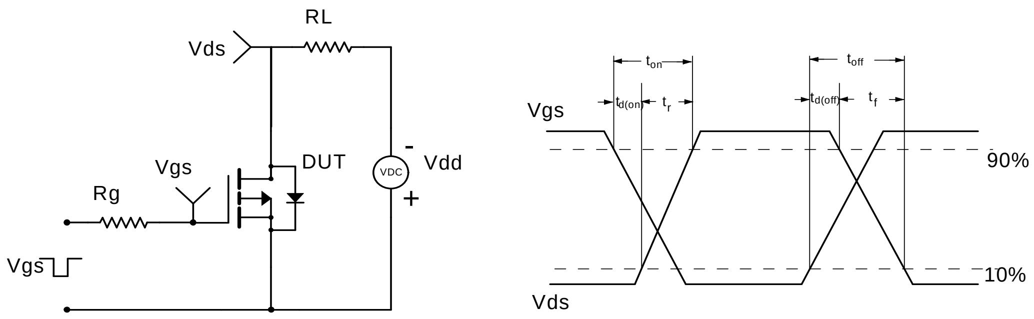
Pulse Width (s)

Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

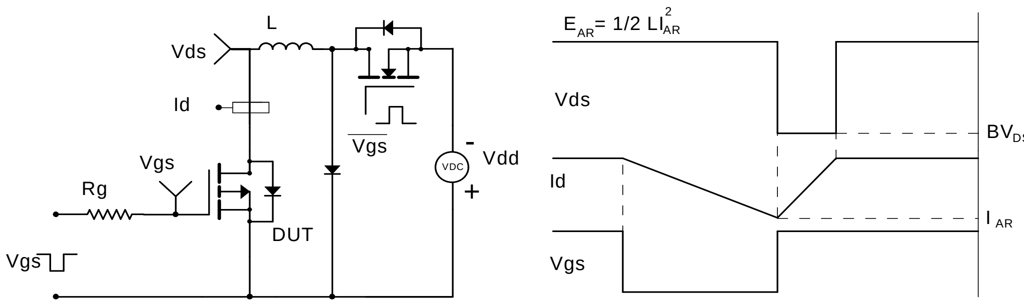
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms